

CLAIMS

subcl *B1* 21. (Amended) A conductive line comprising:
a polysilicon layer;
a metal-silicide layer against the layer of polysilicon, the metal-silicide layer comprising a Group III dopant or a Group V dopant; and
a silicon-dioxide-containing dopant barrier layer against the metal-silicide layer.

22. The conductive line of claim 21 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1×10^{18} ions/cm³.

23. ~~Cancel.~~

24. ~~Cancel.~~

25. ~~Cancel.~~

26. ~~Cancel.~~

27. ~~Cancel.~~

28. ~~Cancel.~~

rubcd 29. (New) The conductive line of claim 21 wherein the silicon-dioxide-containing dopant barrier layer is elevationally above the metal-silicide layer.

30. (New) The conductive line of claim 21 wherein the metal-silicide layer comprises an elevationally uppermost surface relative to the polysilicon layer, and wherein the silicon-dioxide-containing dopant barrier layer is against the uppermost surface.

BA 31. (New) The conductive line of claim 21 wherein the metal-silicide layer comprises an elevationally uppermost surface relative to the polysilicon layer, the uppermost surface having a width dimension, and wherein the silicon-dioxide-containing dopant barrier layer is against substantially the entire width of the uppermost surface.